

26. (Amended) The thin film transistor including a plurality of component parts comprising:

- a channel region;
- a gate electrode opposed to the channel region;
- a gate insulating film provided between the channel region and the gate electrode;
- a source-drain region connected to said channel region;
- a source-drain wiring layer electrically connected to said source-drain region;
- a gate wiring layer electrically connected to said gate electrode,
- wherein the channel region includes an outwardly extending extension.

32. (Amended) The thin film transistor according to Claim 25, wherein the channel region includes an outwardly extending extension.

37. (Amended) The thin film transistor according to Claim 25 or 26, the formed extension extending in a direction substantially perpendicular to a longitudinal direction.

39. (Amended) The display device according to Claim 38, the formed extension extending in a direction substantially perpendicular to a longitudinal direction.

43. (Amended) A liquid crystal display device according to Claim 38, the formed extension extending in a direction substantially perpendicular to a longitudinal direction.

44. (Amended) A thin film transistor including a plurality of component parts comprising:

- a channel region;
- a gate electrode opposed to the channel region;
- a gate insulating film provided between the channel region and the gate electrode;
- a source-drain region connected to said channel region;
- a source-drain wiring layer electrically connected to said source-drain region;
- a gate wiring layer electrically connected to said gate electrode,

comprising an extension extending outwardly from a part of at least one of the gate wiring layer and the source-drain wiring layer, the part having two contact holes with which another contact hole is aligned.

45. (Amended) The thin film transistor according to claim 44, an extension of the gate electrode extending outwardly above the channel region.

46. (Amended) The thin film transistor according to claim 44, wherein the channel region includes an outwardly extending extension.

Please add new claims 47-56 as follows:

Fig. 5
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--47. A thin film transistor including a plurality of component parts comprising:

- a channel region;
- a gate electrode opposed to the channel region;
- a gate insulating film provided between the channel region and the gate electrode;
- a source-drain region connected to said channel region;
- a source-drain wiring layer electrically connected to said source-drain region;

and

- a gate wiring layer electrically connected to said gate electrode,
- at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, said radiating extension extending outwardly from both sides of said gate electrode and is provided on at least one end of said gate electrode; and
- wherein said gate wiring layer is electrically connected to the radiating extension of said gate electrode by a plurality of contact holes. --

Fig. 5

--48. A thin film transistor including a plurality of component parts comprising:

- a channel region;
- a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region;

and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, said radiating extension extending from both sides of said channel region; and

said radiating extension extending from both sides of said source-drain region and said source-drain wiring layer is electrically connected to the radiating extension of said source-drain region by a plurality of contact holes.--

--49. A thin film transistor including a plurality of component parts comprising:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region;

and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, said radiating extension extending from both sides of said source-drain region and wherein said source-drain wiring layer electrically connected to the radiating extension of said source-drain region by a plurality of contact holes.--

--50. A CMOS inverter circuit, comprising:

two thin film transistors, each thin film transistor including a plurality of component parts that include:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region;

and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, said radiating extension extending from both sides of said source-drain region, said thin film transistors having an inverse conductivity type from each other, adjacent source-drain regions of said thin film transistors being connected.--

--51. A CMOS inverter circuit, comprising:

two thin film transistors, each thin film transistor including a plurality of component parts that include:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region;

and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, wherein said radiating extension extends from both sides of said source-drain region, said thin film transistors having an inverse conductivity type from each other, adjacent source-drain regions of said thin film transistors being connected,

wherein said radiating extension is provided with a conductivity by using an impurity identical to an impurity of said source-drain region to which said radiating extension is connected.--

--52. A CMOS inverter circuit, comprising:

two thin film transistors, each thin film transistor including a plurality of component parts that include:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region;

and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, said radiating extension extends from both sides of said source-drain region, said thin film transistors having an inverse conductivity type from each other, adjacent source-drain regions of said thin film transistors being connected;

wherein said radiating extension is formed in a region opposed to said source-drain wiring layer, said source-drain wiring layer connecting the adjacent source-drain regions of said thin film transistors.--

--53. A liquid crystal display device comprising:

an active matrix substrate;

a driving circuit formed on the active matrix substrate and including a CMOS inverter circuit, the liquid crystal display device includes:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region;

and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, wherein said radiating extension extends from both sides of said source-drain region, said thin film transistors having an inverse conductivity type from each other, adjacent source-drain regions of said thin film transistors being connected;

forming a liquid crystal display device comprising an active matrix substrate on which a driving circuit including a CMOS inverter.--

--54. An electronic apparatus comprising a CMOS inverter circuit, the CMOS inverter circuit having two thin film transistors, each thin film transistor includes:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region;

and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, wherein said radiating extension extends from both sides of said source-drain region, said thin film transistors having an inverse conductivity type from each other, adjacent source-drain regions of said thin film transistors being connected;

an electronic apparatus comprising a CMOS inverter circuit.--

--55. A liquid crystal display device comprising:

an active matrix substrate;

a driving circuit formed on the active matrix substrate and including a CMOS inverter circuit, the liquid crystal display device includes:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region;

and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, wherein said radiating extension extends from both sides of said source-drain region, said thin film transistors having an inverse conductivity type from each other, adjacent source-drain regions of said thin film transistors being connected;

forming a liquid crystal display device comprising an active matrix substrate on which a driving circuit including a CMOS inverter;

said plurality of component parts each extending in a longitudinal direction, the radiating extension extending in a direction substantially perpendicular to the longitudinal direction.--

--56. An electronic apparatus comprising a CMOS inverter circuit, the CMOS inverter circuit having two thin film transistors, each thin film transistor includes:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region;

and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, wherein said radiating extension extends from both sides of said source-drain region, said thin film transistors having an inverse conductivity type from each other, adjacent source-drain regions of said thin film transistors being connected;

an electronic apparatus comprising a CMOS inverter circuit;

said plurality of component parts each extending in a longitudinal direction, the radiating extension extending in a direction substantially perpendicular to the longitudinal direction.--
